

MGBR20V150C

Preliminary

DIODE

DUAL MOS GATED BARRIER RECTIFIER

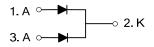
DESCRIPTION

The UTC MGBR20V150C is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

FEATURES

* Very low forward voltage drop * High switching speed

SYMBOL

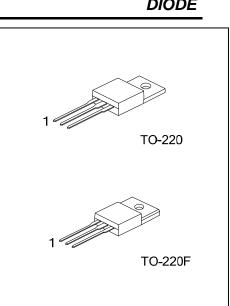


ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR20V150CL-TA3-T	MGBR20V150CG-TA3-T	TO-220	А	К	А	Tube	
MGBR20V150CL-TF3-T	MGBR20V150CG-TF3-T	TO-220F	Α	К	Α	Tube	

Note: Pin Assignment: A: Anode, K: Cathode

MGBR20V150CL- <u>TA3-T</u> (1)Packing Type	(1) T: Tube
(2)Package Type	(2) TA3: TO-220, TF3: TO-220F
(3)Lead Free	(3) L: Lead Free, G: Halogen Free



■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20 %.						
PARAMETER	SYMBOL	RATINGS	UNIT			
DC Blocking Voltage	V _{RM}	150	V			
Working Peak Reverse Voltage	V _{RWM}	150	V			
Peak Repetitive Reverse Voltage	V _{RRM}	150	V			
Average Restified Output Current Day Davies Per Leg	l _o	10	А			
Average Rectified Output Current Per Device Total		20	А			
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	l _{FSM}	150	А			
Operating Junction Temperature	TJ	-65~+150	°C			
Storage Temperature	T _{STG}	-65~+150	°C			

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ _{JA}	62.5	°C/W
Junction to Case	TO-220	0	2	°C/M
	TO-220F	θις	3.31	°C/W

ELECTRICAL CHARACTERISTICS (PER LEG) (T_A=25°C unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	V _{(BR)R}	I _R =0.50mA	150			V
Forward Voltage Drop	Ven	I _F =10A, T _J =25°C			0.85	V
		I _F =10A, T _J =125°C			0.80	V
Leakage Current (Note 1)	RM	V _R =150V, T _J =25°C			100	μA
		V _R =150V, T _J =125°C			30	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

2. Thermal resistance junction to case mounted on heatsink.



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